

**Notice of References Cited**

Application/Control No.

09/944,981

Applicant(s)/Patent Under  
Reexamination  
AHN ET AL.

Examiner

Walter L. Lindsay, Jr.

Art Unit

2812

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kwo et al., Properties of high K gate dielectrics Gd2O3 and Y2O3 for Si, 10/16/00, Journal of Applied Physics, Volume 89 No. 7 pp 3920-3927
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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